Applied Surface Science 46 (1990) 455–460
North-Holland

Author index

Aarnink, W.A.M., see Gao 46 (1990) 74
Afonso, C.N., R. Serna, F. Catalina and D. Bermejo, Good-quality Ge films grown by excimer laser deposition 46 (1990) 249
Afonso, C.N., see Solis 46 (1990) 383
Afonso, C.N., see Serna 46 (1990) 405
Agafonov, A.I. and T.M. Makhviladze, Mechanisms of photon-stimulated desorption and chemisorption of atomic particles on the surfaces of semiconductors and metals 46 (1990) 288
Allen, J.T., see Pemble 46 (1990) 32
Ameen, M.S., see Krauss 46 (1990) 67
Andersen, L.-U.A. and J. Bøttiger, Crystallization of Fe–Zr metallic glasses during ion irradiation 46 (1990) 427
Aubreton, J., see Girault 46 (1990) 78
Auciello, O., see Krauss 46 (1990) 67

Bachmann, F.G., Industrial laser applications 46 (1990) 254
Bahners, T., see Kesting 46 (1990) 326
Baller, T.S., J.C.S. Kools and J. Dieleman, Surface temperature measurements using pyrometry during excimer laser pulsed etching of silicon in a Cl_2 environment 46 (1990) 292
Barfknecht, A.T., see Bernhardt 46 (1990) 121
Barr, T., see Krauss 46 (1990) 67
Bauer, A., J. Ganz, K. Hesse and E. Köhler, Laser-assisted deposition for electronic packaging applications 46 (1990) 113
Bebelaar, D., see Elders 46 (1990) 215
Beech, F., see Sajjadi 46 (1990) 84
Bensoussan, M., see Nissim 46 (1990) 175
Berden, W.C.M., see Giardini-Guidoni 46 (1990) 321
Bermejo, D., see Afonso 46 (1990) 249
Bernhardt, A.F., A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems 46 (1990) 121
Biermann, S., see Buerhop 46 (1990) 430
Blumenthal, B., see Buerhop 46 (1990) 430
Bode, M., E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation 46 (1990) 148
Boelle, A., J.A. Roger, B. Canut, J. Mugnier and M. Pitaval, Sol–gel low-temperature preparation of silica films: RBS, TEM and MOS C–V characterization 46 (1990) 200
Boiteux, G., see Davenas 46 (1990) 330
Bolle, M., K. Luther, J. Troe, J. Ihlemann and H. Gerhardt, Photochemically assisted laser ablation of doped polymethyl-methacrylate 46 (1990) 279
Bollmann, D., see Pielmeier 46 (1990) 163
Bollmann, D., see Stock 46 (1990) 348
Bollmann, D., see Hu 46 (1990) 388
Booth, J.P., see Raynaud 46 (1990) 435
Bostanjoglo, O. and P. Thomsen-Schmidt, Time-resolved TEM of laser-induced structural changes in GeTe films 46 (1990) 392
Bøttiger, J., see Andersen 46 (1990) 427
Boulmer-Leborgne, C., see Hermann 46 (1990) 315
Boyd, I.W., see Sajjadi 46 (1990) 84
Boyd, I.W., see Patel 46 (1990) 352
Bradley, D.C., New metallo-organic precursors for surface processing 46 (1990) 1
Bradshaw, A.M., see Radhakrishnan 46 (1990) 36
Braichotte, D., C. Garrido and H. van den Bergh, The photolytic laser chemical vapor deposition rate of platinum, its dependence on wavelength, precursor vapor pressure, light intensity, and laser beam diameter 46 (1990) 9
Brase, B., see Heidberg 46 (1990) 44
Breuer, J., S. Metev, G. Sepold, O.-D. Hennemann, H. Kollek and G. Krüger, Laser-induced photochemical adherence enhancement 46 (1990) 336
Broussoux, D., see Davenas 46 (1990) 330
Buchner, R., see Stock 46 (1990) 348
Buchner, R., see Hu 46 (1990) 388
Buerhop, C., B. Blumenthal, R. Weissmann, N. Lutz and S. Biermann, Glass surface treatment with excimer and CO_2 lasers 46 (1990) 430
Buhaenko, D.S., see Pemble 46 (1990) 32
Bureau, J.M., see Davenas 46 (1990) 330
Buschick, K., see Müller 46 (1990) 143
Busmann, H.-G., see Ulmer 46 (1990) 272

Cabrera, M., see Zouari 46 (1990) 411
Calvo, M., see Zouari 46 (1990) 411
Campbell, E.E.B., see Ulmer 46 (1990) 272
Canut, B., see Boelle 46 (1990) 200
Catalina, F., see Afonso 46 (1990) 249
Catalina, F., see Solis 46 (1990) 383

Elsevier Science Publishers B.V. (North-Holland)

Catalina, F., see Serna 46 (1990) 405
Catherinot, A., see Girault 46 (1990) 78
Caudano, R., see Petit 46 (1990) 357
Champeaux, C., see Girault 46 (1990) 78
Chapeaublanc, J.-F., see Petitjean 46 (1990) 189
Conrad, H., see Radhakrishnan 46 (1990) 36
Contolini, R.J., see Bernhardt 46 (1990) 121
Curcio, F., M. Musci, N. Notaro and G. De Michele, Synthesis of ultrafine TiO_2 powders by a CW CO_2 laser 46 (1990) 225

Da Silva, M.F., see Serna 46 (1990) 405
Damiani, D., see Girault 46 (1990) 78
D'Anna, E., G. Leggieri, A. Luches, M. Martino, A.V. Drigo, G. Majni, P. Mengucci and I.N. Mihailescu, Nitridation of titanium by multipulse excimer laser irradiation 46 (1990) 365
Davenas, J., G. Boiteux, J.M. Bureau and D. Broussoux, Ion-beam-assisted formation of interconnections into high temperature polymers 46 (1990) 330
De Michele, G., see Curcio 46 (1990) 225
De Unamuno, S., see Elliq 46 (1990) 378
Desimoni, E., see Giardini-Guidoni 46 (1990) 321
Dieleman, J., see Baller 46 (1990) 292
Dilhac, J.-M., N. Nolhier and C. Ganibal, In situ silicon solid state regrowth kinetics measurement in a rapid thermal processor 46 (1990) 451
Drigo, A.V., see D'Anna 46 (1990) 365
Dubreuil, B., see Hermann 46 (1990) 315
Dupuis, V., M.F. Ravet, C. Tête and M. Piecuch, Thermal evolution of W/Si and W/C multilayers under pulsed laser heating and classical annealing 46 (1990) 398
Dyer, P.E., A. Issa and P.H. Key, An investigation of laser ablation and deposition of Y–Ba–Cu–O in an oxygen environment 46 (1990) 89

Elders, J., D. Bebelaar and J.D.W. van Voorst, Photochemical vapor deposition of titaniumdiboride 46 (1990) 215
Eleftheriadis, N., H.-P. Ludescher, M. Süssbauer and D. von der Linde, Picosecond time-resolved laser desorption 46 (1990) 284
Elliq, M., E. Fogarassy, J.P. Stoquert, C. Fuchs, S. de Unamuno, B. Prévot and H. Pattyn, Pulsed excimer and Nd:YAG laser crystallization of a-Si:H. The specific role of hydrogen 46 (1990) 378
Engemann, J., see Korzec 46 (1990) 299
Engemann, J., see Hütten 46 (1990) 306
Esrom, H., see Wahl 46 (1990) 96
Esrom, H. and U. Kogelschatz, Investigation of the mechanism of the UV-induced palladium deposition process from thin solid palladium acetate films 46 (1990) 158
Esser, A., W. Kütt, M. Strahnen, G. Maidorn and H. Kurz, Femtosecond transient reflectivity measurements as a probe for process-induced defects in silicon 46 (1990) 446

Fantoni, R., see Giardini-Guidoni 46 (1990) 321
Fernández, D., see Szörényi 46 (1990) 206
Ferreira, I., see Zeman 46 (1990) 245
Filiouguine, I.V., see Jadin 46 (1990) 375
Fogarassy, E., A. Slaoui, C. Fuchs and J.P. Stoquert, Deposition of SiO_2 by reactive excimer laser ablation from a SiO target 46 (1990) 195
Fogarassy, E., see Elliq 46 (1990) 378
Francis, S.M., see Pemble 46 (1990) 32
Freltoft, T., see Vase 46 (1990) 61
Fuchs, C., see Fogarassy 46 (1990) 195
Fuchs, C., see Elliq 46 (1990) 378

Ganibal, C., see Dilhac 46 (1990) 451
Ganz, J., see Bauer 46 (1990) 113
Gao, J., W.A.M. Aarnink, G.J. Gerritsma and H. Rogalla, High quality $YBa_2Cu_3O_x$ ultra-thin films and Y/Pr/Y multilayers made by a modified RF-magnetron sputtering technique 46 (1990) 74
Garrido, C., see Braichotte 46 (1990) 9
Geerts, M.J., see Zeman 46 (1990) 245
Gerhardt, H., see Bolle 46 (1990) 279
Germain, C., see Girault 46 (1990) 78
Gerritsma, G.J., see Gao 46 (1990) 74
Giardini-Guidoni, A., see Teghil 46 (1990) 220
Giardini-Guidoni, A., A. Morone, M. Snels, E. Desimoni, A.M. Salvi, R. Fantoni, W.C.M. Berden and M. Giorgi, Luminescence and ESCA analysis of laser-ablated materials 46 (1990) 321
Giorgi, M., see Giardini-Guidoni 46 (1990) 321
Girault, C., D. Damiani, C. Champeaux, P. Marchet, C. Germain, J.P. Mercurio, J. Aubreton and A. Catherinot, Characterization of the KrF laser-induced plasma plume created above an YBaCuO superconducting target and preparation of superconducting thin films 46 (1990) 78
Golusda, E., R. Lange, G. Mollekopf and H. Stafast, On the role of the substrate position in the CO_2 laser CVD of amorphous hydrogenated silicon 46 (1990) 230
González, P., see Szörényi 46 (1990) 206
Goulding, P.A., see Pemble 46 (1990) 32
Graettinger, T.M., see Krauss 46 (1990) 67
Gruen, D.M., see Krauss 46 (1990) 67

Haberger, K., see Pielmeier 46 (1990) 163
Haberger, K., see Stock 46 (1990) 348
Haberger, K., see Hu 46 (1990) 388
Hage Ali, M., see Marfaing 46 (1990) 422
Han, B., see Interrante 46 (1990) 5
Hartiti, B., A. Slaoui, J.C. Muller and P. Siffert, Annealing kinetics during rapid thermal processing of excimer laser-induced defects in virgin silicon 46 (1990) 371
Hasselberger, B., see Ulmer 46 (1990) 272
Heidberg, J., B. Brase, K.-W. Stahmer and M. Suhren, Second harmonic generation of CO_2-laser radiation and FTIR spectroscopy for resonant desorption in the adsorbate CO–NaCl-(100) 46 (1990) 44
Hennemann, O.-D., see Breuer 46 (1990) 336
Hermann, J., C. Boulmer-Leborgne and B. Dubreuil, Spectroscopic study of the plasma created by interaction between a TEA CO_2 laser beam and a Ti target in a cell containing helium gas 46 (1990) 315
Hesch, K., P. Hess, H. Oetzmann and C. Schmidt, Laser CVD of a-Si:H from SiH_4 and Si_2H_6: relations between chemistry, growth rate and film properties 46 (1990) 233
Hess, P., see Konstantinov 46 (1990) 102
Hess, P., see Hesch 46 (1990) 233
Hesse, K., see Bauer 46 (1990) 113
Hiraoka, H. and S. Lazare, Surface modifications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization 46 (1990) 264
Hiraoka, H. and S. Lazare, Applications of doping and dedoping of Teflon AF films in microfabrication using KrF and ArF excimer lasers 46 (1990) 342
Horiike, Y., T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method 46 (1990) 168
Houzay, F., see Nissim 46 (1990) 175
Hu, B., A. Seidl, R. Buchner, D. Bollmann, W. van der Wel and K. Haberger, Investigation of laser recrystallization of thin Si films using numerical simulation 46 (1990) 388
Huber, R., see Schmaderer 46 (1990) 53
Hudson, J.B., see Interrante 46 (1990) 5
Hütten, H.M., K.-D. Raddatz, M.K. Sharma and J. Engemann, On the two- and three-dimensional simulation of ion-milled structures 46 (1990) 306

Ichihara, T., see Horiike 46 (1990) 168
Ihlemann, J., see Bolle 46 (1990) 279
Interrante, L.V., B. Han, J.B. Hudson and C. Whitmarsh, Design and synthesis of CVD precursors to thin film ceramic materials 46 (1990) 5
Issa, A., see Dyer 46 (1990) 89

Jadin, A., I.V. Fitiouguine, M. Wautelet and L.D. Laude, Influence of the substrate on the temperature induced by pulsed laser irradiation of thin films 46 (1990) 375

Kessler, T., see Korzec 46 (1990) 299
Kesting, W., T. Bahners and E. Schollmeyer, Controlled structuring of polymer surfaces by UV-laser irradiation 46 (1990) 326
Key, P.H., see Dyer 46 (1990) 89
Kingon, A.I., see Krauss 46 (1990) 67
Kishida, S., see Morishige 46 (1990) 108
Kitamura, S., see Morishige 46 (1990) 108
Klumpp, A., see León 46 (1990) 210
Kogelschatz, U., see Esrom 46 (1990) 158
Köhler, E., see Bauer 46 (1990) 113
Kolev, K., M. Wautelet and L.D. Laude, CW laser-induced transformation of thin Sb, Se and Sb_2Se_3 films in air 46 (1990) 418
Kollek, H., see Breuer 46 (1990) 336
Konstantinov, L., R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD 46 (1990) 102
Kools, J.C.S., see Baller 46 (1990) 292
Korzec, D., T. Kessler and J. Engemann, Reactive ion beam etching of Si/SiO_2 systems using SF_6/O_2 chemistry 46 (1990) 299
Krans, R.L., see Van Maaren 46 (1990) 138
Krauss, A.R., O. Auciello, A.I. Kingon, M.S. Ameen, Y.L. Liu, T. Barr, T.M. Graettinger, S.H. Rou, C.S. Soble and D.M. Gruen, Computer-controlled ion beam deposition systems for high T_c superconductor and other multi-component oxide thin films and layered structures 46 (1990) 67
Kreutz, E.W., see Bode 46 (1990) 148
Krösche, M., see Bode 46 (1990) 148
Krüger, G., see Breuer 46 (1990) 336
Kuen-Lau, K., see Sajjadi 46 (1990) 84
Kurz, H., see Esser 46 (1990) 446
Kütt, W., see Esser 46 (1990) 446

Lange, R., see Golusda 46 (1990) 230
Lapicque, F., see Zouari 46 (1990) 411
Larciprete, R., Photoprocesses in organometallics 46 (1990) 19
Laude, L.D., see Jadin 46 (1990) 375
Laude, L.D., see Kolev 46 (1990) 418
Lazare, S., see Hiraoka 46 (1990) 264
Lazare, S., see Hiraoka 46 (1990) 342

Lebland, F., see Nissim 46 (1990) 175
Lee, J., see Pemble 46 (1990) 32
Leggieri, G., see D'Anna 46 (1990) 365
León, B., see Szörényi 46 (1990) 206
León, B., A. Klumpp, M. Pérez-Amor and H. Sigmund, Excimer laser deposition of silica films: a comparison between two methods 46 (1990) 210
Licoppe, C., see Nissim 46 (1990) 175
Liu, Y.L., see Krauss 46 (1990) 67
Luches, A., see D'Anna 46 (1990) 365
Ludescher, H.-P., see Eleftheriadis 46 (1990) 284
Luther, K., see Bolle 46 (1990) 279
Lutz, N., see Buerhop 46 (1990) 430

Maidorn, G., see Esser 46 (1990) 446
Majni, G., see D'Anna 46 (1990) 365
Makhviladze, T.M., see Agafonov 46 (1990) 288
Malba, V., see Bernhardt 46 (1990) 121
Marchet, P., see Girault 46 (1990) 78
Marfaing, J., see Marine 46 (1990) 239
Marfaing, J., W. Marine, B. Vidal, M. Toulemonde, M. Hage Ali and J.P. Stoquert, Instability and structural transformation of amorphous ultra-thin W–Si multilayer structures during heavy ion irradiation 46 (1990) 422
Marine, W., J.M. Scotto D'Aniello and J. Marfaing, Picosecond YAG laser photoablation of amorphous silicon 46 (1990) 239
Marine, W., see Marfaing 46 (1990) 422
Martino, M., see D'Anna 46 (1990) 365
Mayer, S.T., see Bernhardt 46 (1990) 121
Mele, A., see Teghil 46 (1990) 220
Mengucci, P., see D'Anna 46 (1990) 365
Mercurio, J.P., see Girault 46 (1990) 78
Metev, S., see Breuer 46 (1990) 336
Metselaar, J.W., see Zeman 46 (1990) 245
Mihailescu, I.N., see D'Anna 46 (1990) 365
Moison, J.M., see Nissim 46 (1990) 175
Mollekopf, G., see Golusda 46 (1990) 230
Morishige, Y., S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD 46 (1990) 108
Morone, A., see Giardini-Guidoni 46 (1990) 321
Mugnier, J., see Boelle 46 (1990) 200
Müller, H.G., K. Buschick, S. Schuler and A. Paredes, Laser direct writing of copper on various thin-film substrate materials 46 (1990) 143
Muller, J.C., see Hartiti 46 (1990) 371
Musci, M., see Curcio 46 (1990) 225

Neumayer, G., see Stock 46 (1990) 348
Nissim, Y.I., J.M. Moison, F. Houzay, F. Lebland, C. Licoppe and M. Bensoussan, Photo-assisted deposition of thin films on III–V semiconductors with UV and IR lamps 46 (1990) 175
Nolhier, N., see Dilhac 46 (1990) 451
Notaro, N., see Curcio 46 (1990) 225
Nowak, R., see Konstantinov 46 (1990) 102

Oetzmann, H., see Schmaderer 46 (1990) 53
Oetzmann, H., see Hesch 46 (1990) 233

Paredes, A., see Müller 46 (1990) 143
Parrott, M.J., see Pemble 46 (1990) 32
Patel, P. and I.W. Boyd, Low temperature VUV enhanced growth of thin silicon dioxide films 46 (1990) 352
Pattyn, H., see Elliq 46 (1990) 378
Pemble, M.E., J.T. Allen, D.S. Buhaenko, S.M. Francis, P.A. Goulding, J. Lee and M.J. Parrott, The adsorption of triethylgallium on GaAs(100) at 300 K: adsorption kinetics from optical second harmonic generation transients 46 (1990) 32
Pérez-Amor, M., see Szörényi 46 (1990) 206
Pérez-Amor, M., see León 46 (1990) 210
Perrin, J., see Petitjean 46 (1990) 189
Persch, G., see Strecker 46 (1990) 441
Petit, E.J. and R. Caudano, Chemical reactions at solid–solid interfaces induced by pulsed laser annealing 46 (1990) 357
Petitjean, M., N. Proust, J.-F. Chapeaublanc and J. Perrin, SiO_2 deposition by direct photolysis at 185 nm of N_2O and SiH_4 46 (1990) 189
Petzold, H.-C., see Putzar 46 (1990) 131
Piccirillo, S., see Teghil 46 (1990) 220
Piecuch, M., see Dupuis 46 (1990) 398
Pielmeier, R., D. Bollmann and K. Haberger, Laser evaporation of metal sandwich layers for improved IC metallization 46 (1990) 163
Pitaval, M., see Boelle 46 (1990) 200
Polla-Mattiot, F., see Teghil 46 (1990) 220
Pomot, C., see Raynaud 46 (1990) 435
Pou, J., see Szörényi 46 (1990) 206
Prévot, B., see Elliq 46 (1990) 378
Proust, N., see Petitjean 46 (1990) 189
Putzar, R., H.-C. Petzold and H. Staiger, Optimization of the laser-induced deposition technique for its application in X-ray mask repair 46 (1990) 131

Raddatz, K.-D., see Hütten 46 (1990) 306
Radhakrishnan, G., W. Stenzel, H. Conrad and A.M. Bradshaw, Photoreactions of adsorbed CH_3Br on Pt(111) 46 (1990) 36
Raley, N.F., see Bernhardt 46 (1990) 121
Ravet, M.F., see Dupuis 46 (1990) 398

Raynaud, P., J.P. Booth and C. Pomot, Hydrogen plasma treatment of silicon surfaces studied by in-situ spectroscopic ellipsometry 46 (1990) 435
Rogalla, H., see Gao 46 (1990) 74
Roger, J.A., see Boelle 46 (1990) 200
Rou, S.H., see Krauss 46 (1990) 67

Saba, F., see Sajjadi 46 (1990) 84
Sajjadi, A., K. Kuen-Lau, F. Saba, F. Beech and I.W. Boyd, Laser-ablation deposition of uniform thin films of $Bi_2Sr_2CaCu_2O_x$ 46 (1990) 84
Sakaue, H., see Horiike 46 (1990) 168
Salvi, A.M., see Giardini-Guidoni 46 (1990) 321
Schmaderer, F., R. Huber, H. Oetzmann and G. Wahl, High-T_c $YBa_2Cu_3O_{7-\delta}$ prepared by chemical vapour deposition 46 (1990) 53
Schmidt, C., see Hesch 46 (1990) 233
Schollmeyer, E., see Kesting 46 (1990) 326
Schuler, S., see Müller 46 (1990) 143
Scotto D'Aniello, J.M., see Marine 46 (1990) 239
Seidl, A., see Hu 46 (1990) 388
Sepold, G., see Breuer 46 (1990) 336
Serna, R., see Afonso 46 (1990) 249
Serna, R., C.N. Afonso, F. Catalina, N. Teixeira, M.F. da Silva and J.C. Soares, Diffusion and microstructures induced by excimer laser irradiation in Ge–Sb thin film bilayers 46 (1990) 405
Sharma, M.K., see Hütten 46 (1990) 306
Shen Yueqiang, see Vase 46 (1990) 61
Siffert, P., see Hartiti 46 (1990) 371
Sigmund, H., see León 46 (1990) 210
Simpson, J. and J.O. Williams, Preferential (111) orientation of ZnSe on (100) GaAs deposited by laser-induced MOCVD 46 (1990) 27
Sinke, W.C., see Van Maaren 46 (1990) 138
Slaoui, A., see Fogarassy 46 (1990) 195
Slaoui, A., see Hartiti 46 (1990) 371
Snels, M., see Giardini-Guidoni 46 (1990) 321
Soares, J.C., see Serna 46 (1990) 405
Soble, C.S., see Krauss 46 (1990) 67
Solis, J., C.N. Afonso and F. Catalina, The influence of the substrate on the transformations induced in Si by nanosecond laser irradiation: a time-resolved study 46 (1990) 383
Stafast, H., see Golusda 46 (1990) 230
Stahmer, K.-W., see Heidberg 46 (1990) 44
Staiger, H., see Putzar 46 (1990) 131
Stenzel, W., see Radhakrishnan 46 (1990) 36
Stock, G., D. Bollmann, R. Buchner, G. Neumayer and K. Haberger, Ultra-flat p–n junctions formed by solid source laser doping 46 (1990) 348
Stoquert, J.P., see Fogarassy 46 (1990) 195
Stoquert, J.P., see Elliq 46 (1990) 378
Stoquert, J.P., see Marfaing 46 (1990) 422
Strahnen, M., see Esser 46 (1990) 446
Strecker, H. and G. Persch, Scanning tunneling microscopy and technical applications 46 (1990) 441
Stuke, M., see Zhang 46 (1990) 153
Suhren, M., see Heidberg 46 (1990) 44
Süssbauer, M., see Eleftheriadis 46 (1990) 284
Szörényi, T., P. González, D. Fernández, J. Pou, B. León and M. Pérez-Amor, Gas mixture dependence of the LCVD of SiO_2 films using an ArF laser 46 (1990) 206

Teghil, R., A. Giardini-Guidoni, S. Piccirillo, A. Mele and F. Polla-Mattiot, In situ formation of ionic carbide clusters by laser ablation 46 (1990) 220
Teixeira, N., see Serna 46 (1990) 405
Tête, C., see Dupuis 46 (1990) 398
Thomsen-Schmidt, P., see Bostanjoglo 46 (1990) 392
Toulemonde, M., see Marfaing 46 (1990) 422
Troe, J., see Bolle 46 (1990) 279
Tuckerman, D.B., see Bernhardt 46 (1990) 121

Ulmer, G., B. Hasselberger, H.-G. Busmann and E.E.B. Campbell, Excimer laser ablation of polyimide 46 (1990) 272

Van den Bergh, H., see Braichotte 46 (1990) 9
Van der Wel, W., see Hu 46 (1990) 388
Van Maaren, A.J.P., R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of tungsten 46 (1990) 138
Van Voorst, J.D.W., see Elders 46 (1990) 215
Vase, P., Shen Yueqiang and T. Freltoft, Deposition, characterization, and laser ablation patterning of YBCO thin films 46 (1990) 61
Vidal, B., see Marfaing 46 (1990) 422
Von der Linde, D., see Eleftheriadis 46 (1990) 284

Wahl, G., see Schmaderer 46 (1990) 53
Wahl, G. and H. Esrom, Simulation of laser CVD 46 (1990) 96
Wautelet, M., see Jadin 46 (1990) 375
Wautelet, M., see Kolev 46 (1990) 418
Weissmann, R., see Buerhop 46 (1990) 430
Whitmarsh, C., see Interrante 46 (1990) 5
Williams, J.O., see Simpson 46 (1990) 27

Zeman, M., I. Ferreira, M.J. Geerts and J.W. Metselaar, The influence of deposition parameters on the growth of a-SiGe:H alloys in a plasma CVD system 46 (1990) 245

Zhang, Y. and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for metallic surface patterning 46 (1990) 153

Zouari, I., M. Calvo, F. Lapicque and M. Cabrera, Morphological improvement of zinc electrodeposits by laser assistance 46 (1990) 411

Applied Surface Science 46 (1990) 461–476
North-Holland

Subject index

Adhesion

J. Breuer, S. Metev, G. Sepold, O.-D. Hennemann, H. Kollek and G. Krüger, Laser-induced photochemical adherence enhancement 46 (1990) 336

Adsorption isotherms

M.E. Pemble, J.T. Allen, D.S. Buhaenko, S.M. Francis, P.A. Goulding, J. Lee and M.J. Parrott, The adsorption of triethylgallium on GaAs(100) at 300 K: adsorption kinetics from optical second harmonic generation transients 46 (1990) 32

J. Heidberg, B. Brase, K.-W. Stahmer and M. Suhren, Second harmonic generation of CO_2-laser radiation and FTIR spectroscopy for resonant desorption in the adsorbate CO–NaCl(100) 46 (1990) 44

Alkali halides

J. Heidberg, B. Brase, K.-W. Stahmer and M. Suhren, Second harmonic generation of CO_2-laser radiation and FTIR spectroscopy for resonant desorption in the adsorbate CO–NaCl(100) 46 (1990) 44

Alloys

R. Pielmeier, D. Bollmann and K. Haberger, Laser evaporation of metal sandwich layers for improved IC metallization 46 (1990) 163

Aluminium

E.J. Petit and R. Caudano, Chemical reactions at solid–solid interfaces induced by pulsed laser annealing 46 (1990) 357

Amorphous materials

E. Golusda, R. Lange, G. Mollekopf and H. Stafast, On the role of the substrate position in the CO_2 laser CVD of amorphous hydrogenated silicon 46 (1990) 230

K. Hesch, P. Hess, H. Oetzmann and C. Schmidt, Laser CVD of a-Si:H from SiH_4 and Si_2H_6: relations between chemistry, growth rate and film properties 46 (1990) 233

W. Marine, J.M. Scotto D'Aniello and J. Marfaing, Picosecond YAG laser photoablation of amorphous silicon 46 (1990) 239

M. Zeman, I. Ferreira, M.J. Geerts and J.W. Metselaar, The influence of deposition parameters on the growth of a-SiGe:H alloys in a plasma CVD system 46 (1990) 245

H. Hiraoka and S. Lazare, Applications of doping and dedoping of Teflon AF films in microfabrication using KrF and ArF excimer lasers 46 (1990) 342

M. Elliq, E. Fogarassy, J.P. Stoquert, C. Fuchs, S. de Unamuno, B. Prévot and H. Pattyn, Pulsed excimer and Nd:YAG laser crystallization of a-Si:H. The specific role of hydrogen 46 (1990) 378

O. Bostanjoglo and P. Thomsen-Schmidt, Time-resolved TEM of laser-induced structural changes in GeTe films 46 (1990) 392

K. Kolev, M. Wautelet and L.D. Laude, CW laser-induced transformation of thin Sb, Se and Sb_2Se_3 films in air 46 (1990) 418

J. Marfaing, W. Marine, B. Vidal, M. Toulemonde, M. Hage Ali and J.P. Stoquert, Instability and structural transformation of amorphous ultrathin W–Si multilayer structures during heavy ion irradiation 46 (1990) 422

L.-U.A. Andersen and J. Bøttiger, Crystallization of Fe–Zr metallic glasses during ion irradiation 46 (1990) 427

Annealing

B. Hartiti, A. Slaoui, J.C. Muller and P. Siffert, Annealing kinetics during rapid thermal processing of excimer laser-induced defects in virgin silicon 46 (1990) 371

V. Dupuis, M.F. Ravet, C. Tête and M. Piecuch, Thermal evolution of W/Si and W/C multilayers under pulsed laser heating and classical annealing 46 (1990) 398

J.-M. Dilhac, N. Nolhier and C. Ganibal, In situ silicon solid state regrowth kinetics measurement in a rapid thermal processor 46 (1990) 451

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Antimony

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R. Serna, C.N. Afonso, F. Catalina, N. Teixeira, M.F. da Silva and J.C. Soares, Diffusion and microstructures induced by excimer laser irradiation in Ge–Sb thin film bilayers 46 (1990) 405

K. Kolev, M. Wautelet and L.D. Laude, CW laser-induced transformation of thin Sb, Se and Sb_2Se_3 films in air 46 (1990) 418

Atomic and molecular beam studies

L.V. Interrante, B. Han, J.B. Hudson and C. Whitmarsh, Design and synthesis of CVD precursors to thin film ceramic materials 46 (1990) 5

Auger electron spectroscopy

E.J. Petit and R. Caudano, Chemical reactions at solid–solid interfaces induced by pulsed laser annealing 46 (1990) 357

Borides

J. Elders, D. Bebelaar and J.D.W. van Voorst, Photochemical vapor deposition of titaniumdiboride 46 (1990) 215

Boron

G. Stock, D. Bollmann, R. Buchner, G. Neumayer and K. Haberger, Ultra-flat p–n junctions formed by solid source laser doping 46 (1990) 348

Carbides

R. Teghil, A. Giardini-Guidoni, S. Piccirillo, A. Mele and F. Polla-Mattiot, In situ formation of ionic carbide clusters by laser ablation 46 (1990) 220

Carbon

V. Dupuis, M.F. Ravet, C. Tête and M. Piecuch, Thermal evolution of W/Si and W/C multilayers under pulsed laser heating and classical annealing 46 (1990) 398

Carbon monoxide

J. Heidberg, B. Brase, K.-W. Stahmer and M. Suhren, Second harmonic generation of CO_2-laser radiation and FTIR spectroscopy for resonant desorption in the adsorbate CO–NaCl(100) 46 (1990) 44

Ceramics

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Chemical vapour deposition

D.C. Bradley, New metallo-organic precursors for surface processing 46 (1990) 1

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D. Braichotte, C. Garrido and H. van den Bergh, The photolytic laser chemical vapor deposition rate of platinum, its dependence on wavelength, precursor vapor pressure, light intensity, and laser beam diameter 46 (1990) 9

R. Larciprete, Photoprocesses in organometallics 46 (1990) 19

J. Simpson and J.O. Williams, Preferential (111) orientation of ZnSe on (100) GaAs deposited by laser-induced MOCVD 46 (1990) 27

F. Schmaderer, R. Huber, H. Oetzmann and G. Wahl, High-T_c $YBa_2Cu_3O_{7-\delta}$ prepared by chemical vapour deposition 46 (1990) 53

G. Wahl and H. Esrom, Simulation of laser CVD 46 (1990) 96

L. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD 46 (1990) 102

Y. Morishige, S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD 46 (1990) 108

R. Putzar, H.-C. Petzold and H. Staiger, Optimization of the laser-induced deposition technique for its application in X-ray mask repair 46 (1990) 131

A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of tungsten 46 (1990) 138

Y. Horiike, T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method 46 (1990) 168
Y.I. Nissim, J.M. Moison, F. Houzay, F. Lebland, C. Licoppe and M. Bensoussan, Photo-assisted deposition of thin films on III–V semiconductors with UV and IR lamps 46 (1990) 175
M. Petitjean, N. Proust, J.-F. Chapeaublanc and J. Perrin, SiO_2 deposition by direct photolysis at 185 nm of N_2O and SiH_4 46 (1990) 189
T. Szörényi, P. González, D. Fernández, J. Pou, B. León and M. Pérez-Amor, Gas mixture dependence of the LCVD of SiO_2 films using an ArF laser 46 (1990) 206
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K. Hesch, P. Hess, H. Oetzmann and C. Schmidt, Laser CVD of a-Si:H from SiH_4 and Si_2H_6: relations between chemistry, growth rate and film properties 46 (1990) 233
M. Zeman, I. Ferreira, M.J. Geerts and J.W. Metselaar, The influence of deposition parameters on the growth of a-SiGe:H alloys in a plasma CVD system 46 (1990) 245

Chromium

L. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD 46 (1990) 102

Clusters

R. Teghil, A. Giardini-Guidoni, S. Piccirillo, A. Mele and F. Polla-Mattiot, In situ formation of ionic carbide clusters by laser ablation 46 (1990) 220

Compound formation

E.J. Petit and R. Caudano, Chemical reactions at solid–solid interfaces induced by pulsed laser annealing 46 (1990) 357

Contacts

Y. Morishige, S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD 46 (1990) 108
A.F. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems 46 (1990) 121

Copper

G. Wahl and H. Esrom, Simulation of laser CVD 46 (1990) 96
H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of copper on various thin-film substrate materials 46 (1990) 143
M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation 46 (1990) 148

Crystallization

M. Elliq, E. Fogarassy, J.P. Stoquert, C. Fuchs, S. de Unamuno, B. Prévot and H. Pattyn, Pulsed excimer and Nd:YAG laser crystallization of a-Si:H. The specific role of hydrogen 46 (1990) 378
B. Hu, A. Seidl, R. Buchner, D. Bollmann, W. van der Wel and K. Haberger, Investigation of laser recrystallization of thin Si films using numerical simulation 46 (1990) 388
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J. Marfaing, W. Marine, B. Vidal, M. Toulemonde, M. Hage Ali and J.P. Stoquert, Instability and structural transformation of amorphous ultrathin W–Si multilayer structures during heavy ion irradiation 46 (1990) 422
L.-U.A. Andersen and J. Bøttiger, Crystallization of Fe–Zr metallic glasses during ion irradiation 46 (1990) 427

Diffusion

L. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD 46 (1990) 102

G. Stock, D. Bollmann, R. Buchner, G. Neumayer and K. Haberger, Ultra-flat p–n junctions formed by solid source laser doping 46 (1990) 348
R. Serna, C.N. Afonso, F. Catalina, N. Teixeira, M.F. da Silva and J.C. Soares, Diffusion and microstructures induced by excimer laser irradiation in Ge–Sb thin film bilayers 46 (1990) 405

Doping effects

H. Hiraoka and S. Lazare, Applications of doping and dedoping of Teflon AF films in microfabrication using KrF and ArF excimer lasers 46 (1990) 342
G. Stock, D. Bollmann, R. Buchner, G. Neumayer and K. Haberger, Ultra-flat p–n junctions formed by solid source laser doping 46 (1990) 348

Electrical properties

F. Schmaderer, R. Huber, H. Oetzmann and G. Wahl, High-T_c $YBa_2Cu_3O_{7-\delta}$ prepared by chemical vapour deposition 46 (1990) 53
P. Vase, Shen Yueqiang and T. Freltoft, Deposition, characterization, and laser ablation patterning of YBCO thin films 46 (1990) 61
J. Gao, W.A.M. Aarnink, G.J. Gerritsma and H. Rogalla, High quality $YBa_2Cu_3O_x$ ultra-thin films and Y/Pr/Y multilayers made by a modified RF-magnetron sputtering technique 46 (1990) 74
Y. Morishige, S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD 46 (1990) 108
A.F. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems 46 (1990) 121
M. Petitjean, N. Proust, J.-F. Chapeaublanc and J. Perrin, SiO_2 deposition by direct photolysis at 185 nm of N_2O and SiH_4 46 (1990) 189
A. Boelle, J.A. Roger, B. Canut, J. Mugnier and M. Pitaval, Sol–gel low-temperature preparation of silica films: RBS, TEM and MOS *C–V* characterization 46 (1990) 200
K. Hesch, P. Hess, H. Oetzmann and C. Schmidt, Laser CVD of a-Si:H from SiH_4 and Si_2H_6: relations between chemistry, growth rate and film properties 46 (1990) 233
M. Zeman, I. Ferreira, M.J. Geerts and J.W. Metselaar, The influence of deposition parameters on the growth of a-SiGe:H alloys in a plasma CVD system 46 (1990) 245
J. Davenas, G. Boiteux, J.M. Bureau and D. Broussoux, Ion-beam-assisted formation of interconnections into high temperature polymers 46 (1990) 330

Electron diffraction

F. Curcio, M. Musci, N. Notaro and G. De Michele, Synthesis of ultrafine TiO_2 powders by a CW CO_2 laser 46 (1990) 225
E. D'Anna, G. Leggieri, A. Luches, M. Martino, A.V. Drigo, G. Majni, P. Mengucci and I.N. Mihailescu, Nitridation of titanium by multipulse excimer laser irradiation 46 (1990) 365
J. Solis, C.N. Afonso and F. Catalina, The influence of the substrate on the transformations induced in Si by nanosecond laser irradiation: a time-resolved study 46 (1990) 383
V. Dupuis, M.F. Ravet, C. Tête and M. Piecuch, Thermal evolution of W/Si and W/C multilayers under pulsed laser heating and classical annealing 46 (1990) 398
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Electron energy loss spectroscopy

G. Radhakrishnan, W. Stenzel, H. Conrad and A.M. Bradshaw, Photoreactions of adsorbed CH_3Br on Pt(111) 46 (1990) 36

Electron microscopy

F. Schmaderer, R. Huber, H. Oetzmann and G. Wahl, High-T_c $YBa_2Cu_3O_{7-\delta}$ prepared by chemical vapour deposition 46 (1990) 53
A.R. Krauss, O. Auciello, A.I. Kingon, M.S. Ameen, Y.L. Liu, T. Barr, T.M. Graettinger, S.H. Rou, C.S. Soble and D.M. Gruen, Computer-controlled ion beam deposition systems for high T_c

superconductor and other multi-component oxide thin films and layered structures 46 (1990) 67

P.E. Dyer, A. Issa and P.H. Key, An investigation of laser ablation and deposition of Y–Ba–Cu–O in an oxygen environment 46 (1990) 89

Y. Morishige, S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD 46 (1990) 108

A. Bauer, J. Ganz, K. Hesse and E. Köhler, Laser-assisted deposition for electronic packaging applications 46 (1990) 113

A.F. Bernhardt, A.T. Barfknecht, R.J. Contolini, V. Malba, S.T. Mayer, N.F. Raley and D.B. Tuckerman, Multichip packaging for very-high-speed digital systems 46 (1990) 121

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M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation 46 (1990) 148

R. Pielmeier, D. Bollmann and K. Haberger, Laser evaporation of metal sandwich layers for improved IC metallization 46 (1990) 163

Y. Horiike, T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method 46 (1990) 168

E. Fogarassy, A. Slaoui, C. Fuchs and J.P. Stoquert, Deposition of SiO_2 by reactive excimer laser ablation from a SiO target 46 (1990) 195

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K. Hesch, P. Hess, H. Oetzmann and C. Schmidt, Laser CVD of a-Si:H from SiH_4 and Si_2H_6: relations between chemistry, growth rate and film properties 46 (1990) 233

M. Zeman, I. Ferreira, M.J. Geerts and J.W. Metselaar, The influence of deposition parameters on the growth of a-SiGe:H alloys in a plasma CVD system 46 (1990) 245

C.N. Afonso, R. Serna, F. Catalina and D. Bermejo, Good-quality Ge films grown by excimer laser deposition 46 (1990) 249

H. Hiraoka and S. Lazare, Surface modifications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization 46 (1990) 264

M. Bolle, K. Luther, J. Troe, J. Ihlemann and H. Gerhardt, Photochemically assisted laser ablation of doped polymethyl-methacrylate 46 (1990) 279

D. Korzec, T. Kessler and J. Engemann, Reactive ion beam etching of Si/SiO_2 systems using SF_6/O_2 chemistry 46 (1990) 299

H.M. Hütten, K.-D. Raddatz, M.K. Sharma and J. Engemann, On the two- and three-dimensional simulation of ion-milled structures 46 (1990) 306

W. Kesting, T. Bahners and E. Schollmeyer, Controlled structuring of polymer surfaces by UV-laser irradiation 46 (1990) 326

J. Davenas, G. Boiteux, J.M. Bureau and D. Broussoux, Ion-beam-assisted formation of interconnections into high temperature polymers 46 (1990) 330

J. Breuer, S. Metev, G. Sepold, O.-D. Hennemann, H. Kollek and G. Krüger, Laser-induced photochemical adherence enhancement 46 (1990) 336

H. Hiraoka and S. Lazare, Applications of doping and dedoping of Teflon AF films in microfabrication using KrF and ArF excimer lasers 46 (1990) 342

E.J. Petit and R. Caudano, Chemical reactions at solid–solid interfaces induced by pulsed laser annealing 46 (1990) 357

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J. Solis, C.N. Afonso and F. Catalina, The influence of the substrate on the transformations induced in Si by nanosecond laser irradiation: a time-resolved study 46 (1990) 383

O. Bostanjoglo and P. Thomsen-Schmidt,

Time-resolved TEM of laser-induced structural changes in GeTe films 46 (1990) 392
V. Dupuis, M.F. Ravet, C. Tête and M. Piecuch, Thermal evolution of W/Si and W/C multilayers under pulsed laser heating and classical annealing 46 (1990) 398
R. Serna, C.N. Afonso, F. Catalina, N. Teixeira, M.F. da Silva and J.C. Soares, Diffusion and microstructures induced by excimer laser irradiation in Ge–Sb thin film bilayers 46 (1990) 405
I. Zouari, M. Calvo, F. Lapicque and M. Cabrera, Morphological improvement of zinc electrodeposits by laser assistance 46 (1990) 411
J. Marfaing, W. Marine, B. Vidal, M. Toulemonde, M. Hage Ali and J.P. Stoquert, Instability and structural transformation of amorphous ultrathin W–Si multilayer structures during heavy ion irradiation 46 (1990) 422
C. Buerhop, B. Blumenthal, R. Weissmann, N. Lutz and S. Biermann, Glass surface treatment with excimer and CO_2 lasers 46 (1990) 430

Ellipsometry

T. Szörényi, P. González, D. Fernández, J. Pou, B. León and M. Pérez-Amor, Gas mixture dependence of the LCVD of SiO_2 films using an ArF laser 46 (1990) 206
B. León, A. Klumpp, M. Pérez-Amor and H. Sigmund, Excimer laser deposition of silica films: a comparison between two methods 46 (1990) 210
P. Raynaud, J.P. Booth and C. Pomot, Hydrogen plasma treatment of silicon surfaces studied by in-situ spectroscopic ellipsometry 46 (1990) 435

Etching

Y. Morishige, S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD 46 (1990) 108
Y. Horiike, T. Ichihara and H. Sakaue, Filling of Si oxide into a deep trench using digital CVD method 46 (1990) 168
W. Marine, J.M. Scotto D'Aniello and J. Marfaing, Picosecond YAG laser photoablation of amorphous silicon 46 (1990) 239
G. Ulmer, B. Hasselberger, H.-G. Busmann and E.E.B. Campbell, Excimer laser ablation of polyimide 46 (1990) 272
M. Bolle, K. Luther, J. Troe, J. Ihlemann and H. Gerhardt, Photochemically assisted laser ablation of doped polymethyl-methacrylate 46 (1990) 279
T.S. Baller, J.C.S. Kools and J. Dieleman, Surface temperature measurements using pyrometry during excimer laser pulsed etching of silicon in a Cl_2 environment 46 (1990) 292
D. Korzec, T. Kessler and J. Engemann, Reactive ion beam etching of Si/SiO_2 systems using SF_6/O_2 chemistry 46 (1990) 299

Gallium arsenide

N. Eleftheriadis, H.-P. Ludescher, M. Süssbauer and D. von der Linde, Picosecond time-resolved laser desorption 46 (1990) 284

Germanium

M. Zeman, I. Ferreira, M.J. Geerts and J.W. Metselaar, The influence of deposition parameters on the growth of a-SiGe:H alloys in a plasma CVD system 46 (1990) 245
C.N. Afonso, R. Serna, F. Catalina and D. Bermejo, Good-quality Ge films grown by excimer laser deposition 46 (1990) 249
O. Bostanjoglo and P. Thomsen-Schmidt, Time-resolved TEM of laser-induced structural changes in GeTe films 46 (1990) 392
R. Serna, C.N. Afonso, F. Catalina, N. Teixeira, M.F. da Silva and J.C. Soares, Diffusion and microstructures induced by excimer laser irradiation in Ge–Sb thin film bilayers 46 (1990) 405

Glass

C. Buerhop, B. Blumenthal, R. Weissmann, N. Lutz and S. Biermann, Glass surface treatment with excimer and CO_2 lasers 46 (1990) 430

Halogens

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Hydrogen

P. Raynaud, J.P. Booth and C. Pomot, Hydrogen plasma treatment of silicon surfaces studied by in-situ spectroscopic ellipsometry 46 (1990) 435

Infrared spectroscopy

J. Heidberg, B. Brase, K.-W. Stahmer and M. Suhren, Second harmonic generation of CO_2-laser radiation and FTIR spectroscopy for resonant desorption in the adsorbate CO–NaCl(100) 46 (1990) 44

Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for metallic surface patterning 46 (1990) 153

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Y.I. Nissim, J.M. Moison, F. Houzay, F. Lebland, C. Licoppe and M. Bensoussan, Photo-assisted deposition of thin films on III–V semiconductors with UV and IR lamps 46 (1990) 175

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Interfaces

Y.I. Nissim, J.M. Moison, F. Houzay, F. Lebland, C. Licoppe and M. Bensoussan, Photo-assisted deposition of thin films on III–V semiconductors with UV and IR lamps 46 (1990) 175

E.J. Petit and R. Caudano, Chemical reactions at solid–solid interfaces induced by pulsed laser annealing 46 (1990) 357

Ion bombardment

A.R. Krauss, O. Auciello, A.I. Kingon, M.S. Ameen, Y.L. Liu, T. Barr, T.M. Graettinger, S.H. Rou, C.S. Soble and D.M. Gruen, Computer-controlled ion beam deposition systems for high T_c superconductor and other multi-component oxide thin films and layered structures 46 (1990) 67

H.M. Hütten, K.-D. Raddatz, M.K. Sharma and J. Engemann, On the two- and three-dimensional simulation of ion-milled structures 46 (1990) 306

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L.-U.A. Andersen and J. Bøttiger, Crystallization of Fe–Zr metallic glasses during ion irradiation 46 (1990) 427

Ion implantation

A. Esser, W. Kütt, M. Strahnen, G. Maidorn and H. Kurz, Femtosecond transient reflectivity measurements as a probe for process-induced defects in silicon 46 (1990) 446

Ion scattering

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E. D'Anna, G. Leggieri, A. Luches, M. Martino, A.V. Drigo, G. Majni, P. Mengucci and I.N. Mihailescu, Nitri-

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Iron

L.-U.A. Andersen and J. Bøttiger, Crystallization of Fe–Zr metallic glasses during ion irradiation 46 (1990) 427

Laser processing

D. Braichotte, C. Garrido and H. van den Bergh, The photolytic laser chemical vapor deposition rate of platinum, its dependence on wavelength, precursor vapor pressure, light intensity, and laser beam diameter 46 (1990) 9
R. Larciprete, Photoprocesses in organometallics 46 (1990) 19
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A. Sajjadi, K. Kuen-Lau, F. Saba, F. Beech and I.W. Boyd, Laser-ablation deposition of uniform thin films of $Bi_2Sr_2CaCu_2O_x$ 46 (1990) 84
P.E. Dyer, A. Issa and P.H. Key, An investigation of laser ablation and deposition of Y–Ba–Cu–O in an oxygen environment 46 (1990) 89
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L. Konstantinov, R. Nowak and P. Hess, Gas-phase transport and kinetics in pulsed-laser CVD 46 (1990) 102
Y. Morishige, S. Kitamura and S. Kishida, High performance contact formation in LSI circuit restructuring using visible pulse laser induced ablation and CVD 46 (1990) 108
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M. Bode, E.W. Kreutz and M. Krösche, Direct writing of conducting traces by chemical modification of solid coatings with laser radiation 46 (1990) 148
Y. Zhang and M. Stuke, VUV synchrotron radiation processing of thin palladium acetate spin-on films for metallic surface patterning 46 (1990) 153
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R. Pielmeier, D. Bollmann and K. Haberger, Laser evaporation of metal sandwich layers for improved IC metallization 46 (1990) 163
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R. Teghil, A. Giardini-Guidoni, S. Piccirillo, A. Mele and F. Polla-Mattiot, In situ formation of ionic carbide clusters by laser ablation 46 (1990) 220

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F.G. Bachmann, Industrial laser applications 46 (1990) 254

H. Hiraoka and S. Lazare, Surface modifications of Kapton and cured polyimide films by ArF excimer laser: applications to imagewise wetting and metallization 46 (1990) 264

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H. Hiraoka and S. Lazare, Applications of doping and dedoping of Teflon AF films in microfabrication using KrF and ArF excimer lasers 46 (1990) 342

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E. D'Anna, G. Leggieri, A. Luches, M. Martino, A.V. Drigo, G. Majni, P. Mengucci and I.N. Mihailescu, Nitridation of titanium by multipulse excimer laser irradiation 46 (1990) 365

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K. Kolev, M. Wautelet and L.D. Laude, CW laser-induced transformation of thin Sb, Se and Sb_2Se_3 films in air 46 (1990) 418

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Light scattering

A. Esser, W. Kütt, M. Strahnen, G. Maidorn and H. Kurz, Femtosecond transient reflectivity measurements as a probe for process-induced defects in silicon 46 (1990) 446

Luminescence

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P.E. Dyer, A. Issa and P.H. Key, An investigation of laser ablation and deposition of Y–Ba–Cu–O in an oxygen environment 46 (1990) 89

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Magnetic structures

H. Strecker and G. Persch, Scanning tunneling microscopy and technical applications 46 (1990) 441

Mass spectroscopy

L.V. Interrante, B. Han, J.B. Hudson and C. Whitmarsh, Design and synthesis of CVD precursors to thin film ceramic materials 46 (1990) 5

A.J.P. van Maaren, R.L. Krans and W.C. Sinke, HF formation in laser-induced CVD of tungsten 46 (1990) 138

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N. Eleftheriadis, H.-P. Ludescher, M. Süssbauer and D. von der Linde, Picosecond time-resolved laser desorption 46 (1990) 284

Metals

R. Pielmeier, D. Bollmann and K. Haberger, Laser evaporation of metal sandwich layers for improved IC metallization 46 (1990) 163

Molecular beam epitaxy

D.C. Bradley, New metallo-organic precursors for surface processing 46 (1990) 1

Nitrides

E. D'Anna, G. Leggieri, A. Luches, M. Martino, A.V. Drigo, G. Majni, P. Mengucci and I.N. Mihailescu, Nitridation of titanium by multipulse excimer laser irradiation 46 (1990) 365

Noble gases

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Optical properties

M. Zeman, I. Ferreira, M.J. Geerts and J.W. Metselaar, The influence of deposition parameters on the growth of a-SiGe:H alloys in a plasma CVD system 46 (1990) 245

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J. Solis, C.N. Afonso and F. Catalina, The influence of the substrate on the transformations induced in Si by nanosecond laser irradiation: a time-resolved study 46 (1990) 383

Organic substances

D.C. Bradley, New metallo-organic precursors for surface processing 46 (1990) 1
L.V. Interrante, B. Han, J.B. Hudson and C. Whitmarsh, Design and synthesis of CVD precursors to thin film ceramic materials 46 (1990) 5
D. Braichotte, C. Garrido and H. van den Bergh, The photolytic laser chemical vapor deposition rate of platinum, its dependence on wavelength, precursor vapor pressure, light intensity, and laser beam diameter 46 (1990) 9
R. Larciprete, Photoprocesses in organometallics 46 (1990) 19
J. Simpson and J.O. Williams, Preferential (111) orientation of ZnSe on (100) GaAs deposited by laser-induced MOCVD 46 (1990) 27
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R. Putzar, H.-C. Petzold and H. Staiger, Optimization of the laser-induced deposition technique for its application in X-ray mask repair 46 (1990) 131
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Oxidation

P. Patel and I.W. Boyd, Low temperature VUV enhanced growth of thin silicon dioxide films 46 (1990) 352
K. Kolev, M. Wautelet and L.D. Laude, CW laser-induced transformation of thin Sb, Se and Sb_2Se_3 films in air 46 (1990) 418

Oxides

R. Pielmeier, D. Bollmann and K. Haberger, Laser evaporation of metal sandwich layers for improved IC metallization 46 (1990) 163

Palladium

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H. Esrom and U. Kogelschatz, Investigation of the mechanism of the UV-induced palladium deposition process from thin solid palladium acetate films 46 (1990) 158

Phosphorus

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Photodesorption

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A.I. Agafonov and T.M. Makhviladze, Mechanisms of photon-stimulated desorption and chemisorption of atomic particles on the surfaces of semiconductors and metals 46 (1990) 288

Photoelectron spectroscopy

A. Bauer, J. Ganz, K. Hesse and E. Köhler, Laser-assisted deposition for electronic packaging applications 46 (1990) 113
H.G. Müller, K. Buschick, S. Schuler and A. Paredes, Laser direct writing of copper on various thin-film substrate materials 46 (1990) 143
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Raman scattering

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Reflection spectroscopy

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Secondary ion mass spectroscopy

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Second harmonic generation

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Selenium

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Silicon

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Silicon carbide

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Solid phase epitaxy

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Sputter deposition

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Sputtering

H.M. Hütten, K.-D. Raddatz, M.K. Sharma and J. Engemann, On the two- and three-dimensional simulation of ion-milled structures 46 (1990) 306

Superconductivity

F. Schmaderer, R. Huber, H. Oetzmann and G. Wahl, High-T_c $YBa_2Cu_3O_{7-\delta}$ prepared by chemical vapour deposition 46 (1990) 53
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P.E. Dyer, A. Issa and P.H. Key, An investigation of laser ablation and deposition of Y–Ba–Cu–O in an oxygen environment 46 (1990) 89

Surface defects

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Surface morphology

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W. Kesting, T. Bahners and E. Schollmeyer, Controlled structuring of polymer surfaces by UV-laser irradiation 46 (1990) 326
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Surface phonons and adsorbate vibrations

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A.I. Agafonov and T.M. Makhviladze, Mechanisms of photon-stimulated desorption and chemisorption of atomic particles on the surfaces of semiconductors and metals 46 (1990) 288

Tellurium

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Thermal desorption

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Tin

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